



GT200CU120T2NH

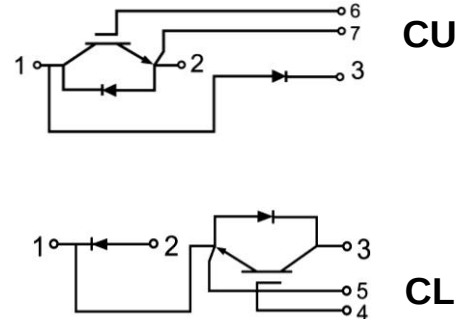
GT200CL120T2NH

IGBT Module

Preliminary Data

Features:

- Field Stop Trench Gate IGBT
- Short Circuit Rated >10 μ s
- Low Saturation Voltage
- Low Switching Loss
- 100% RBSOA Tested(2 $\times$ I_C)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- Industrial Inverters
- Servo Applications
- Power Supply
- Chopper Applications
- Three-level Applications

IGBT, Chopper

Maximum Rated Values (T_C=25°C unless otherwise specified)

V _{CES}	Collector-Emitter Blocking Voltage		1200	V
V _{GES}	Gate-Emitter Voltage		±20	V
I _C	Continuous Collector Current	T _C =100°C	200	A
		T _C =25°C	400	A
I _{CM}	Peak Collector Current Repetitive	t _p =1ms	400	A
P _D	Maximum Power Dissipation (IGBT)	T _C =25°C T _{Jmax} =175°C	1400	W



Electrical Characteristics of IGBT ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Static Characteristics

Symbol	Description	Conditions		Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=7.6\text{mA}$, $V_{CE}=V_{GE}$		5.0	5.8	6.6	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=200\text{A}$, $V_{GE}=15\text{V}$	$T_J=25^{\circ}\text{C}$		1.75	2.00	V
			$T_J=125^{\circ}\text{C}$		2.15		V
			$T_J=150^{\circ}\text{C}$		2.25		V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0\text{V}$, $V_{CE}=V_{CES}$, $T_J=25^{\circ}\text{C}$				1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=\pm 20\text{V}$, $V_{CE}=0\text{V}$, $T_J=25^{\circ}\text{C}$				± 200	nA
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}$, $V_{GE}=0\text{V}$, $f=100\text{kHz}$			22.67		nF
C_{oes}	Output Capacitance				1.20		nF
C_{res}	Reveres Transfer Capacitance				0.32		nF

Switching Characteristics

t _{d(on)}	Turn-on Delay Time	V _{CC} =600V, I _C =200A, R _{Gon} =2Ω, V _{GE} =±15V, Inductive Load	T _J =25℃		194		ns
			T _J =125℃		208		
			T _J =150℃		216		
t _r	Rise Time		T _J =25℃		64		ns
			T _J =125℃		72		
			T _J =150℃		74		
t _{d(off)}	Turn-off Delay Time	V _{CC} =600V, I _C =200A, R _{Goff} =2Ω, V _{GE} =±15V, Inductive Load	T _J =25℃		362		ns
			T _J =125℃		406		
			T _J =150℃		412		
t _f	Fall Time		T _J =25℃		194		ns
			T _J =125℃		218		
			T _J =150℃		236		
E _{on}	Turn-on Switching Loss	V _{CC} =600V, I _C =200A, R _{Gon} =2Ω, V _{GE} =±15V, di/dt=2233A/μs(T _J =150℃), Inductive Load	T _J =25℃		19.0		mJ
			T _J =125℃		35.3		
			T _J =150℃		41.2		



E _{off}	Turn-off Switching Loss	V _{CC} =600V, I _C =200A, R _{Goff} =2Ω, V _{GE} =±15V, du/dt=5121V/μs(T _J =150°C), Inductive Load	T _J =25°C		17.2		mJ
			T _J =125°C		22.9		
			T _J =150°C		24.5		
Q _g	Total Gate Charge	V _{GE} =+15V...-15V	T _J =25°C		2827		nC
R _{G(int)}	Internal Gate Resistor		T _J =25°C		2.75		Ω
I _{SC}	V _{CC} =600V, V _{GE} =+/-15V, t _p =10us, R _{Gon} =47Ω, R _{Goff} =47Ω, T _J =150°C				440		A
R _{θJC}	Thermal Resistance: Junction-to-Case (per IGBT)					0.107	°C/W

Diode, Chopper

Maximum Rated Values (T_C=25°C unless otherwise specified)

V _{RRM}	Repetitive Peak Reverse Voltage	T _J =25°C	1200	V
I _F	Diode Continuous Forward Current	T _C =100°C	200	A
I _{FM}	Peak Diode Current Repetitive	t _p =1ms	400	A

Electrical Characteristics of Diode (T_C=25°C unless otherwise specified)

Symbol	Description	Conditions		Min.	Typ.	Max.	Units
V _{FM}	Forward Voltage	I _F =200A	T _J =25°C		1.70		V
			T _J =125°C		1.80		
			T _J =150°C		1.80		
t _{rr}	Reverse Recovery Time	I _F =200A, -diF/dt=2427A/μs(T _J =150°C), V _R =600V, V _{GE} =-15V	T _J =25°C		288		ns
			T _J =125°C		598		
			T _J =150°C		730		
I _{rr}	Peak Reverse Recovery Current		T _J =25°C		126		A
			T _J =125°C		128		
			T _J =150°C		137		
Q _{rr}	Reverse Recovery Charge		T _J =25°C		19		μC
			T _J =125°C		34		
			T _J =150°C		41		



E _{rec}	Reverse Recovery Energy	I _F =200A, -diF/dt=2427A/μs(T _J =150°C), V _R =600V, V _{GE} =-15V	T _J =25°C		6.57		mJ
			T _J =125°C		11.50		
			T _J =150°C		14.14		
R _{θJC}	Thermal Resistance: Junction-to-Case (per Diode)					0.166	°C/W

Diode, Reverse

Maximum Rated Values of Diode (T_C=25°C unless otherwise specified)

V _{RRM}	Repetitive Peak Reverse Voltage	T _J =25°C	1200	V
I _F	Diode Continuous Forward Current	T _C =100°C	150	A
I _{FM}	Diode Maximum Forward Current	t _p =1ms	300	A

Electrical Characteristics of Diode (T_C=25°C unless otherwise specified)

Symbol	Description	Conditions		Min.	Typ.	Max.	Units
V _{FM}	Forward Voltage	I _F =150A	T _J =25°C		1.50		V
			T _J =125°C		1.55		
			T _J =150°C		1.55		
t _{rr}	Reverse Recovery Time	I _F =150A, -diF/dt=1670A/μs(T _J =150°C), V _R =600V, V _{GE} =-15V	T _J =25°C		471		ns
			T _J =125°C		680		
			T _J =150°C		746		
I _{rr}	Peak Reverse Recovery Current		T _J =25°C		101		A
			T _J =125°C		118		
			T _J =150°C		120		
Q _{rr}	Reverse Recovery Charge		T _J =25°C		15.7		μC
			T _J =125°C		27.8		
			T _J =150°C		31.0		
E _{rec}	Reverse Recovery Energy		T _J =25°C		9.7		mJ
			T _J =125°C		12.5		
			T _J =150°C		14.1		
R _{θJC}	Thermal Resistance: Junction-to-Case (per Diode)					0.205	°C/W



Module

Symbol	Description	Conditions	Min.	Typ.	Max.	Units
V _{iso}	Isolation Voltage (All Terminals Shorted)	f=50Hz, 30s	4500			V
T _J	Maximum Junction Temperature				175	°C
T _{JOP}	Maximum Operating Junction Temperature Range		-40		+150	°C
T _{stg}	Storage Temperature		-40		+150	°C
CTI	Comparative Tracking Index		200			
R _{θCS}	Case-to-Sink Thermally (Conductive Grease Applied)				0.05	°C/W
T	Power Terminals Screw:M6		3.0		5.0	N·m
T	Mounting Screw:M6		4.0		6.0	N·m
G	Weight			300		g

Ordering Information Table

Device code

G	T	200	CU	120	T2N	H
①	②	③	④	⑤	⑥	⑦

- ① - IGBT Module
- ② - Trench, Low Switching Losses IGBT
- ③ - Rated Current (200=200A)
- ④ - Circuit Configuration: Chopper, CU(Diode on High Side) / CL(Diode on Low Side)
- ⑤ - Rated Voltage (120=1200V)
- ⑥ - Package Type
- ⑦ - Test Level (Pass the Important Reliability Test-Industrial Grade)

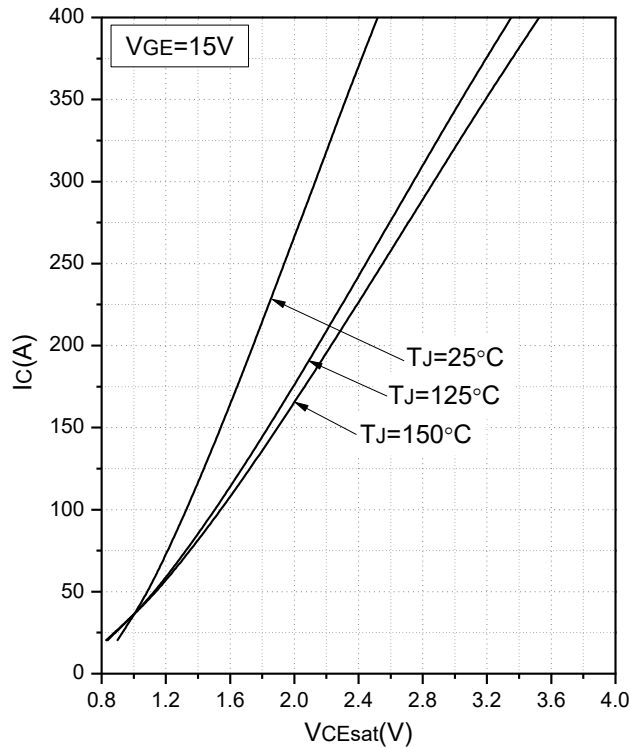


Fig.1 Typical Saturation Voltage Characteristics

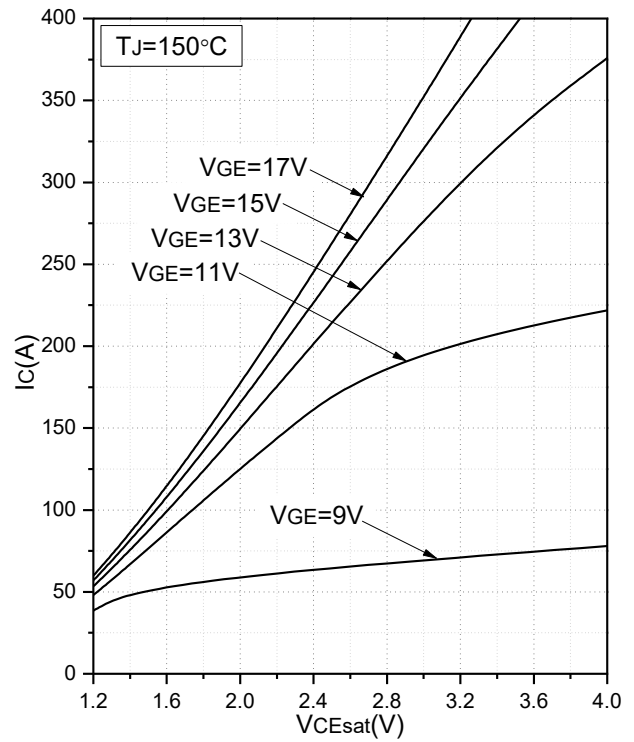


Fig.2 Typical Output Characteristics

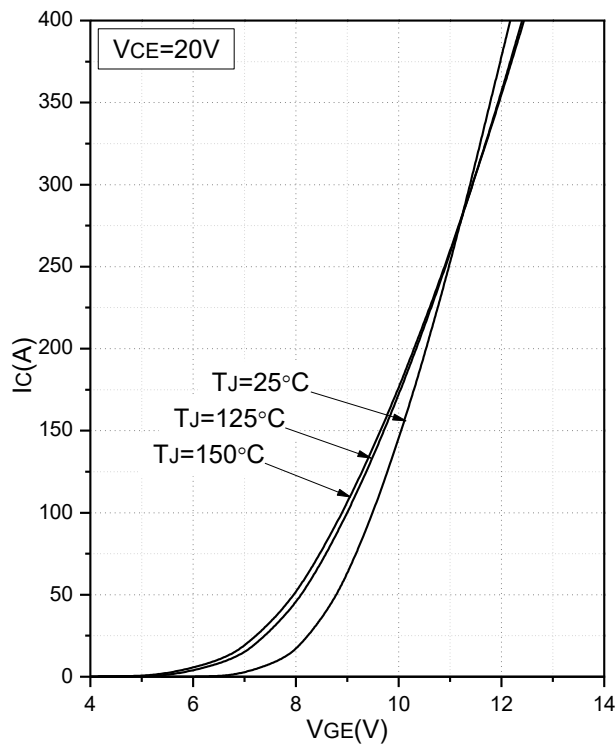


Fig.3 Transfer Characteristics

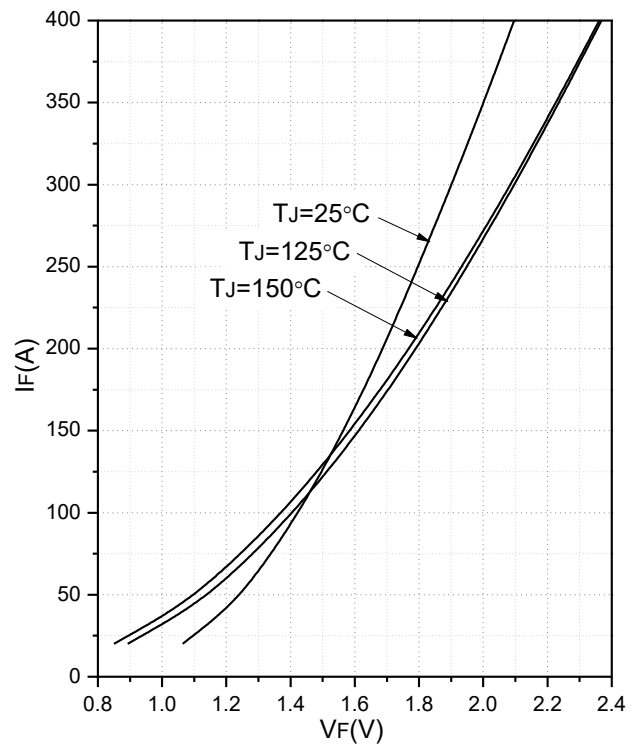


Fig.4 Forward Characteristics of Diode

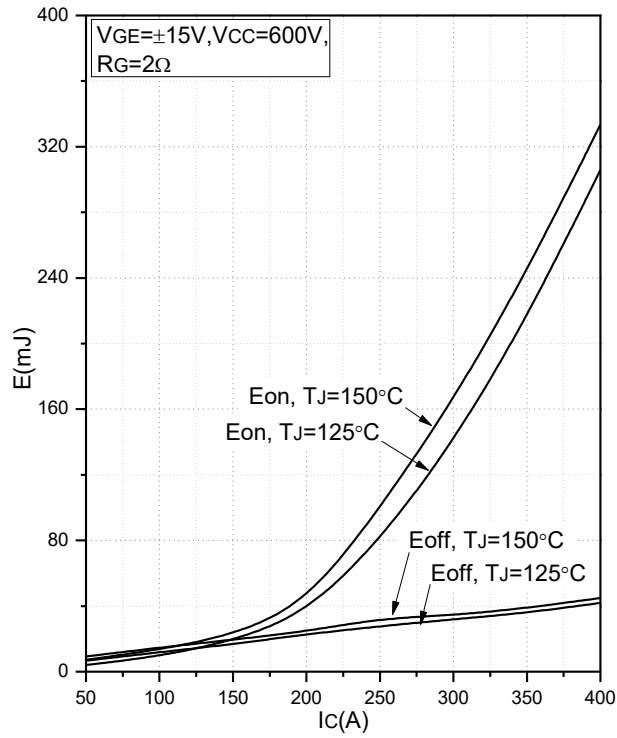


Fig.5 Typical Switching Loss vs. Collector Current

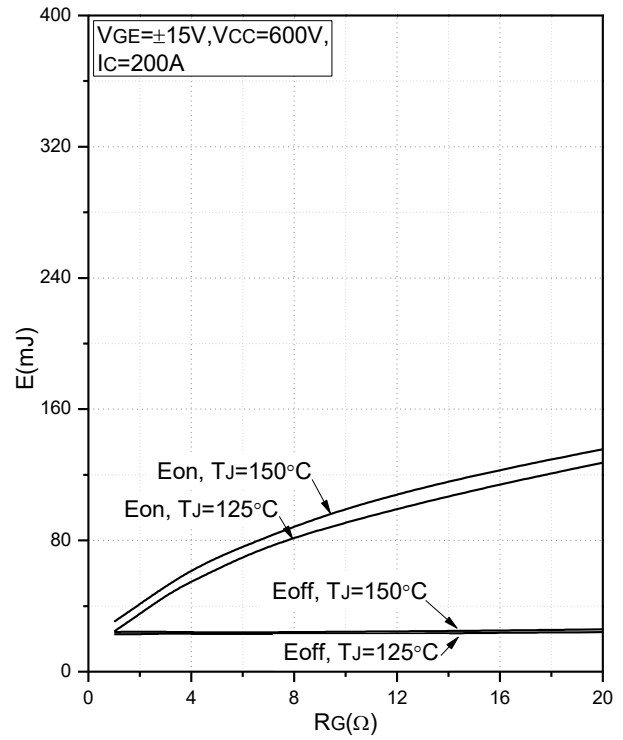


Fig.6 Typical Switching Loss vs. Gate Resistance

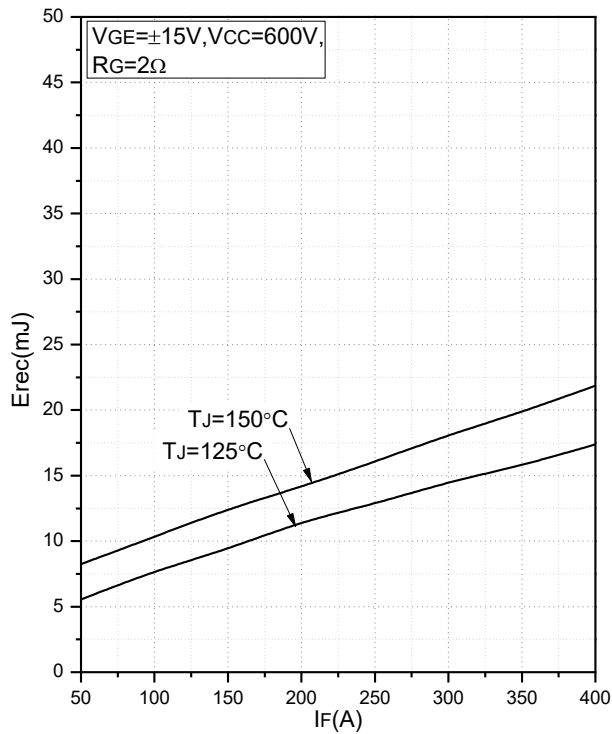


Fig.7 Typical Switching Loss vs. Forward Current

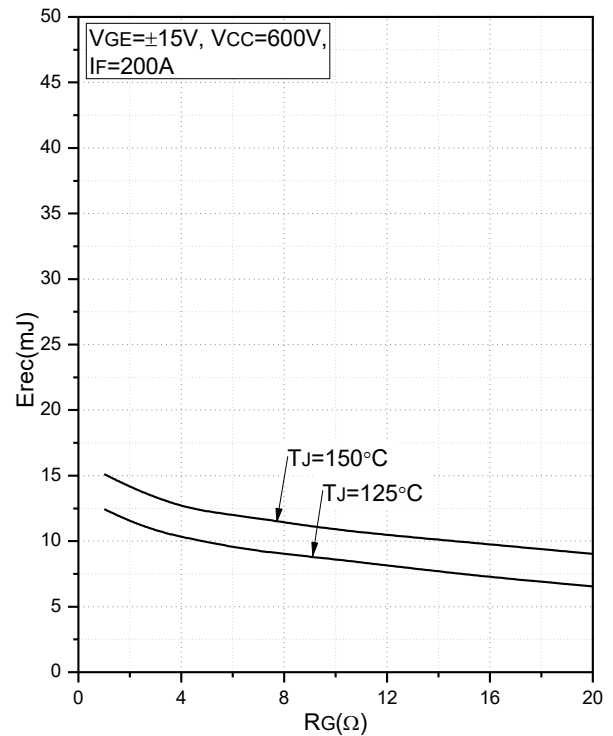


Fig.8 Typical Switching Loss vs. Gate Resistance

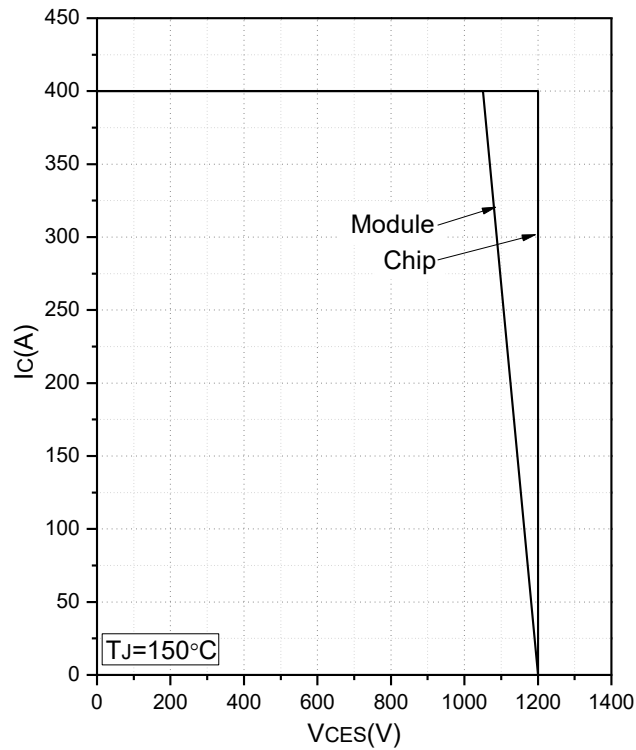


Fig.9 Reverse Bias Safe Operation Area (RBSOA)

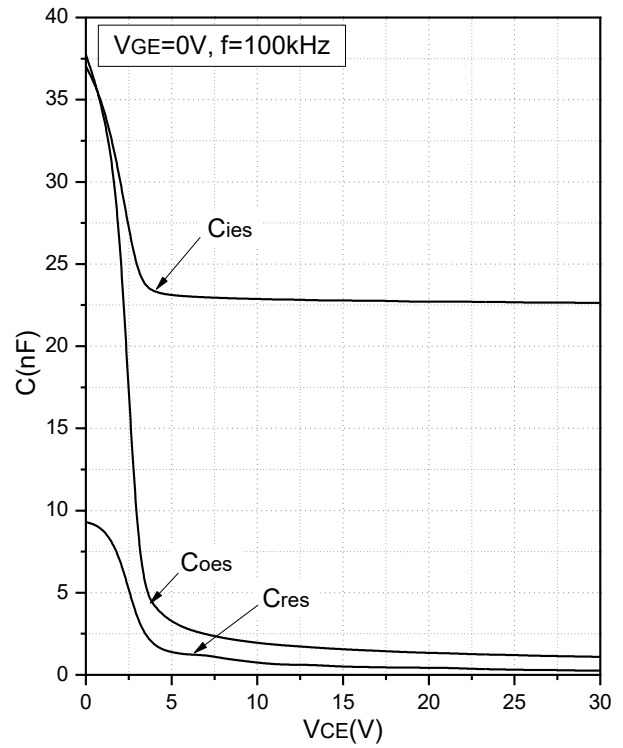


Fig.10 Capacitance Characteristics

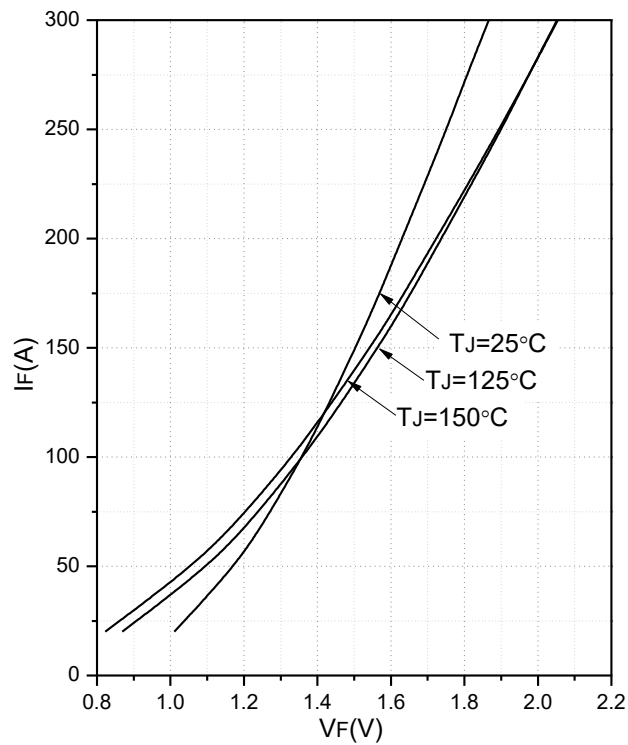


Fig.11 Forward Characteristics of Diode (Reverse)

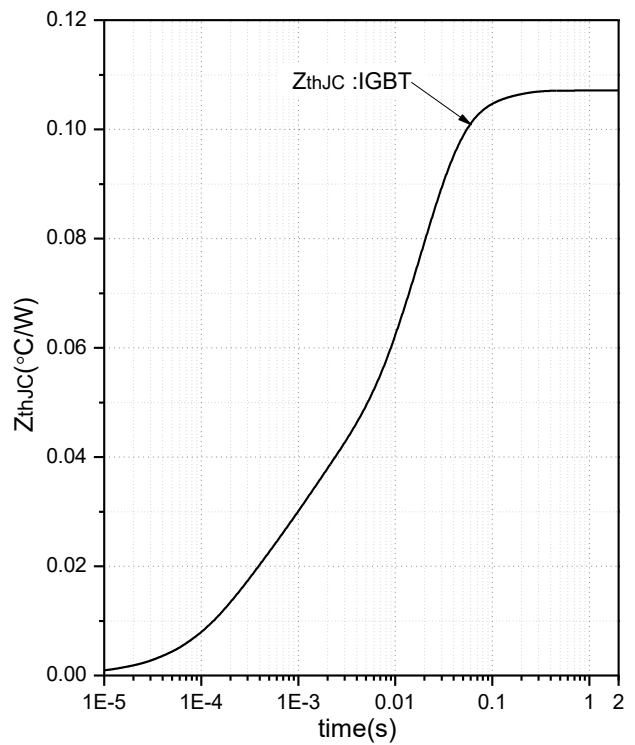


Fig.12 Transient Thermal Impedance (Chopper-IGBT)

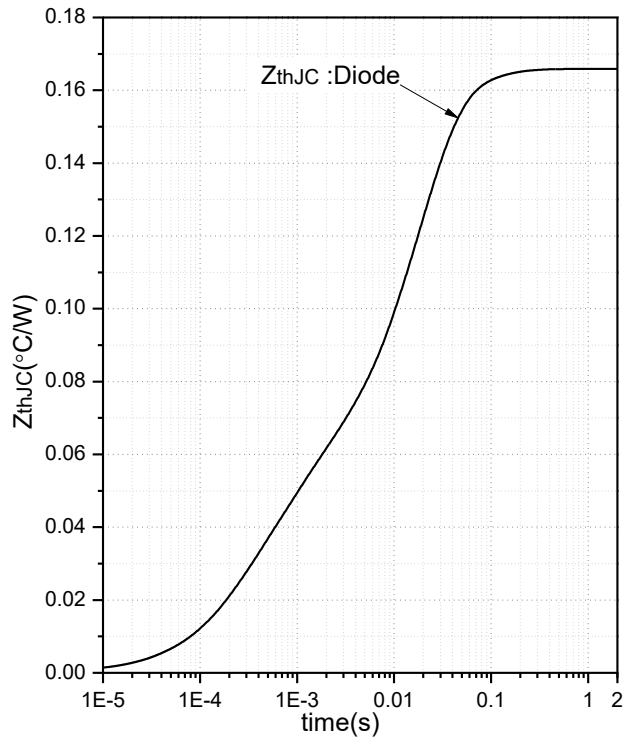


Fig.13 Transient Thermal Impedance (Chopper-Diode)



Revision	Notes
01	Initial release

Announcement

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